MJF31C (NPN), MJF32C (PNP)

Preferred Device

Complementary Silicon Plastic Power Transistors for Isolated Package **Applications**

Designed for use in general purpose amplifier and switching applications.

Features

- Collector-Emitter Saturation Voltage -
 - $V_{CE(sat)} = 1.2 \text{ Vdc (Max)} @ I_C = 3.0 \text{ Adc}$
- Collector-Emitter Sustaining Voltage -
 - $V_{CEO(sus)} = 100 \text{ Vdc (Min)}$
- High Current Gain Bandwidth Product
 - $f_T = 3.0 \text{ MHz (Min)} @ I_C = 500 \text{ mAdc}$
- UL Recognized, File #E69369, to 3500 V_{RMS} Isolation
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	100	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector CurrentUnclamped Inductive Load Energy (Note 1) - Continuous - Peak	lc	3.0 5.0	Adc
Base Current	Ι _Β	1.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	28 0.22	W W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	Е	32	mJ
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JC}$	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.46	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. I_C = 1.8 Å, L = 20 mH, P.R.F. = 10 Hz, V_{CC} = 10 V, R_{BE} = 100 Ω .

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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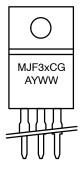
http://onsemi.com

3.0 AMPERE **POWER TRANSISTORS** COMPLEMENTARY SILICON 100 VOLTS, 28 WATTS



TO-220 FULLPAK CASE 221D STYLE 2

MARKING DIAGRAM



= 1 or 2

= Pb-Free Package

= Assembly Location

= Year

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MJF31C	TO-220 FULLPAK	50 Units/Rail
MJF31CG	TO-220 FULLPAK (Pb-Free)	50 Units/Rail
MJF32C	TO-220 FULLPAK	50 Units/Rail
MJF32CG	TO-220 FULLPAK (Pb-Free)	50 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

MJF31C (NPN), MJF32C (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		1		•
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	100	-	Vdc
Collector Cutoff Current (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc)	I _{CEO}	-	0.3	mAdc
Collector Cutoff Current	I _{CES}	-	200	μ Ad c
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	1.0	mAdc
ON CHARACTERISTICS (Note 2)				
DC Current Gain (I_C = 1.0 Adc, V_{CE} = 4.0 Vdc) (I_C = 3.0 Adc, V_{CE} = 4.0 Vdc)	h _{FE}	25 10	- 50	-
Collector-Emitter Saturation Voltage (I _C = 3.0 Adc, I _B = 375 mAdc)	V _{CE(sat)}	-	1.2	Vdc
Base-Emitter On Voltage (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	-	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)	f _T	3.0	-	MHz
Small-Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	20	_	-

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

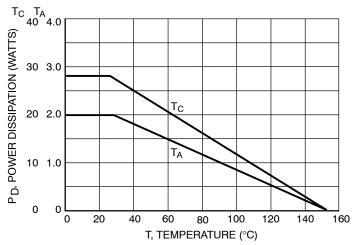
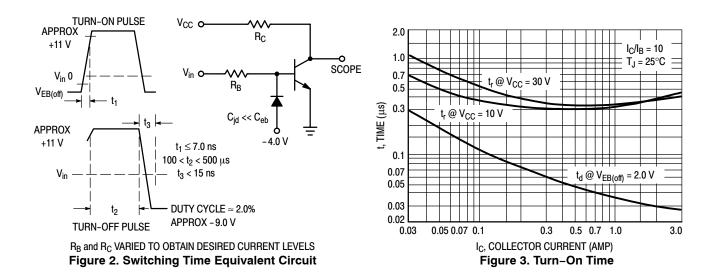


Figure 1. Power Derating



MJF31C (NPN), MJF32C (PNP)

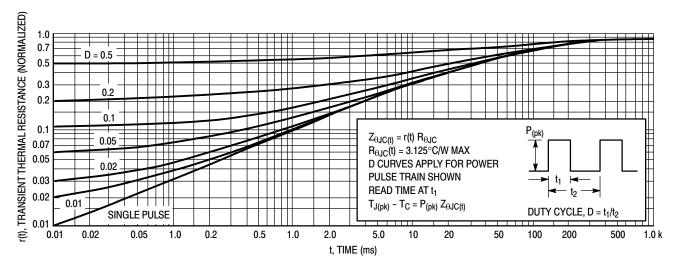


Figure 4. Thermal Response

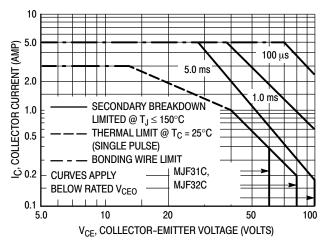


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ} C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

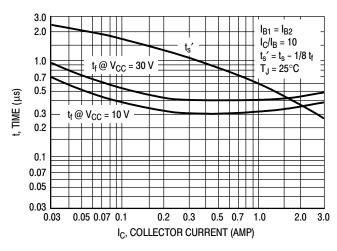


Figure 6. Turn-Off Time

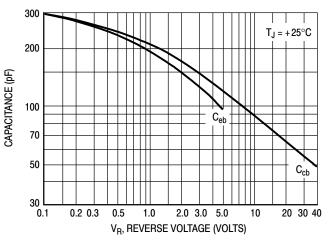
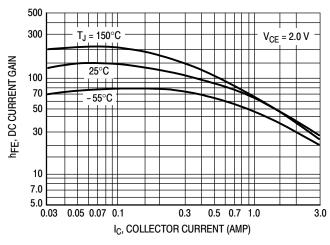


Figure 7. Capacitance

MJF31C (NPN), MJF32C (PNP)



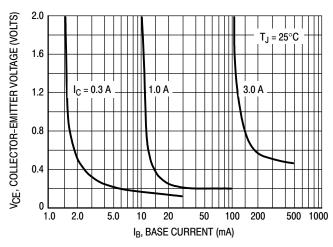
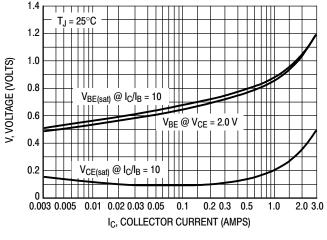


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region



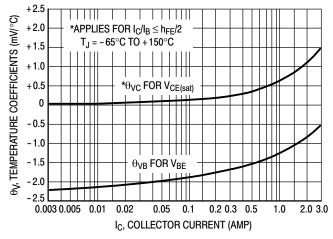
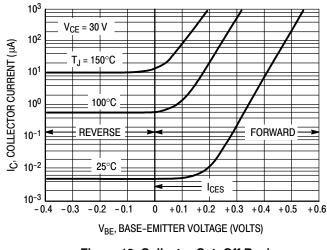


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients



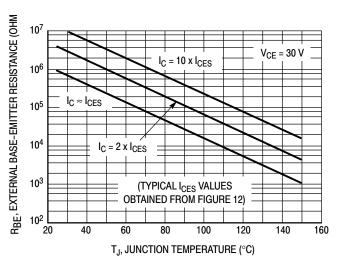


Figure 12. Collector Cut-Off Region

Figure 13. Effects of Base-Emitter Resistance

MECHANICAL CASE OUTLINE





SCALE 1:1

3. CATHODE

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

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AYWW

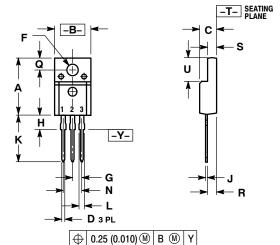
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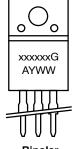
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INC	INCHES		IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

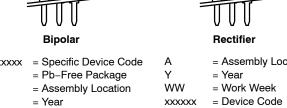
MARKING DIAGRAMS



STYLE 1: PIN 1. GATE STYLE 2: PIN 1. BASE STYLE 3: PIN 1. ANODE 2. COLLECTOR 3. EMITTER CATHODE
 ANODE 2. DRAIN 2. 3. SOURCE STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE



= Assembly Location xxxxxx = Specific Device Code G = Pb-Free Package Υ = Year Α = Assembly Location WW = Work Week Υ = Year XXXXXX = Device Code = Work Week = Pb-Free Package WW G AKA = Polarity Designator



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